

ABSTRACT OF THE DISCLOSURE

There is disclosed an anti-reflection film material used in lithography containing at least a polymer compound having repeating units for copolymerization represented by the following general formula (1), or those containing a polymer compound having repeating units for copolymerization represented by the following general formula (2) and a polymer compound having repeating units for copolymerization represented by the following general formula (3). There can be provided an anti-reflection film material which has an excellent reflection preventive effect to exposure at short wavelength, and has high etch selectivity, namely, an etch rate is higher enough than the photoresist film, an etch rate is sufficiently slower than a substrate to be processed, wherein the shape of the resist pattern formed in the photoresist film on the anti-reflection film can be made perpendicular.

